

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

| APPLICATION NO. | FI | LING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
|----------------------|-----------------------|---------------|----------------------|---------------------|------------------|
| 10/653,152 | 10/653,152 09/03/2003 | | Chandra Mouli | M4065.0970/P970 | 2509 |
| 24998 | 7590 | 12/10/2004 | | EXAM | INER |
| DICKSTEI | N SHAP | IRO MORIN & O | WILSON, ALLAN R | | |
| 2101 L Stree | | 13.7 | ART UNIT | PAPER NUMBER | |
| Washington, DC 20037 | | | | 2815 | |

DATE MAILED: 12/10/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

| 6 | | A) | |
|---|---|--|--|
| | Application No. | Applicant(s) | |
| | 10/653,152 | MOULI, CHANDRA | |
| Office Action Summary | Examiner | Art Unit | |
| | Allan R. Wilson | 2815 | |
| The MAILING DATE of this communication a Period for Reply | appears on the cover sheet w | rith the correspondence address | |
| A SHORTENED STATUTORY PERIOD FOR REF THE MAILING DATE OF THIS COMMUNICATION - Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a r - If NO period for reply is specified above, the maximum statutory perions - Failure to reply within the set or extended period for reply will, by state that the material patent term adjustment. See 37 CFR 1.704(b). | N. R. 1.136(a). In no event, however, may a reply within the statutory minimum of thi iod will apply and will expire SIX (6) MOI atute, cause the application to become A | reply be timely filed irty (30) days will be considered timely. NTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133). | |
| Status | | | |
| 1) Responsive to communication(s) filed on 15 | November 2004. | | |
| 2a) ☐ This action is FINAL . 2b) ☑ TI | his action is non-final. | | |
| 3) Since this application is in condition for allow | wance except for formal mat | ters, prosecution as to the merits is | |
| closed in accordance with the practice unde | r Ex parte Quayle, 1935 C. |). 11, 453 O.G. 213. | |
| Disposition of Claims | | | |
| 4) Claim(s) 1-39 is/are pending in the application | on. | | |
| 4a) Of the above claim(s) <u>9-15 and 21-39</u> is/s | are withdrawn from conside | ration. | |
| 5) Claim(s) is/are allowed. | | | |
| 6) Claim(s) <u>1-8 and 16-20</u> is/are rejected. | | | |
| 7) Claim(s) is/are objected to. | | | |
| 8) Claim(s) are subject to restriction and | d/or election requirement. | | |
| Application Papers | | | |
| 9) The specification is objected to by the Exami | | | |
| 10)☐ The drawing(s) filed on is/are: a)☐ a | | | |
| Applicant may not request that any objection to the | | | |
| Replacement drawing sheet(s) including the corre | | | |
| 11) The oath or declaration is objected to by the | Examiner. Note the attache | d Office Action or form PTO-152. | |
| Priority under 35 U.S.C. § 119 | | | |
| 12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume | ents have been received. ents have been received in A riority documents have been eau (PCT Rule 17.2(a)). | Application No n received in this National Stage | |
| * See the attached detailed Office action for a li | st of the certified copies not | received. | |
| | | | |
| Attachment(s) X Notice of References Cited (PTO-892) | 4) 🗍 Intention | Summary (PTO-413) | |
| 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(| s)/Mail Date | |
| B) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date <u>1004</u> . | 5) Notice of I 6) Other: | Informal Patent Application (PTO-152) | |

DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of Group I, claims 1-8 and 16-20, in the reply filed on 11/15/2004 is acknowledged.

Information Disclosure Statement

The information disclosure statement filed October 8, 2003 fails to comply with the provisions of 37 CFR 1.97, 1.98 and MPEP § 609 because Cite No. CA does not contain a title, author or date. It has been placed in the application file, but the information referred to therein has not been considered as to the merits. Applicant is advised that the date of any re-submission of any item of information contained in this information disclosure statement or the submission of any missing element(s) will be the date of submission for purposes of determining compliance with the requirements based on the time of filing the statement, including all certification requirements for statements under 37 CFR 1.97(e). See MPEP § 609 ¶ C(1).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Application/Control Number: 10/653,152

Art Unit: 2815

Claims 1-8 and 16-20 are rejected under 35 USC § 103 (a) as being unpatentable over McClure, U.S. Patent No. 6,780,666 B1 (or Applicants Prior Art) in view of Tews et al. ("Tews") U.S. Patent No. 6,362,040 B1.

With regards to claim 1, McClure illustrates in figures 1-6, a photosensor 12 having a first doped region 12a and a second doped region 12b in association with a semiconductor substrate 14; an isolation region 32 formed within said substrate.

McClure does not show a halogen-rich region localized at least at a sidewall region of said isolation region. Tews illustrates in at least figure 5 a halogen-rich region localized at least at a sidewall region 123 of an isolation region. It would have been obvious to one of ordinary skill in the art at the time the invention was made to have a halogen-rich region for oxidizing trench sidewalls which reduces crystallographic orientation dependence.

With regards to claim 2, Tews illustrates in fig. 5 said halogen-rich region is in the sidewalls of the trench and therefore when combined with Lin said halogen-rich region will be between said isolation region and said photosensor.

With regards to claims 3 and 17, Tews discloses in col. 5, lines 35-36, said halogen-rich region is formed with an ion selected from the group consisting of fluorine and bromine.

With regards to claim 4 Tews illustrates in fig. 5 said halogen-rich region is in the sidewalls of the trench and therefore when combined with McClure said halogen-rich region and said first doped region 12a of said photosensor will overlap.

With regards to claims 5 and 16, McClure and Tews discloses the claimed invention except for said halogen-rich region has a depth from a surface of said semiconductor substrate of about 300Å to about 800Å. It would have been obvious to one of ordinary skill in the art at the

Application/Control Number: 10/653,152

Art Unit: 2815

time the invention was made to have a depth of 300Å to about 800Å, since it has been held that where the general conditions of a claim are disclosed in the prior art discovering the optimum or working ranges involves only routine skill in the art. In re Aller, 105 USPQ 233.

With regards to claim 6, Tews discloses in col. 5, lines 48-51, said halogen-rich region has a concentration of halogen ions from about 1×10^{14} /cm³ to about 1×10^{15} /cm³.

With regards to claims 7 and 18, McClure illustrates in figures 1-6 a charge collection region 18 electrically connected to readout circuitry 24, 26, 28.

With regards to claims 8 and 19, McClure illustrates in figs. 1-6 a transfer transistor 16 formed between and connecting said photosensor 12 and said charge collection region 18.

With regards to claim 20, McClure illustrates in figs. 1-6 a reset transistor 22 electrically connected to said charge collection region 18.

Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure: Lin (illustrates a photosensor with an isolation trench) and Armacost et al. (illustrates a halogen-rich region in the sidewall of a trench).

| Field of Search | Date |
|--|------------------|
| U.S. Class and subclass: | |
| 257/93, 374, 446 | December 8, 2004 |
| Other Documentation: | |
| None | N/A |
| Electronic data base(s): | |
| EAST (USPAT, US-PGPUB, JPO, EPO, Derwent, IBM TDB) | December 8, 2004 |

Any inquiry concerning this communication or earlier communications from an examiner should be directed to Primary Examiner Allan Wilson whose telephone number is

Art Unit: 2815

(571) 272-1738. Examiner Wilson can normally be reached 7:00-4:00 Monday-Thursday and 6:00-3:00 on Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on (571) 272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Allan R. Wilson

Primary Examiner

8 December 2004